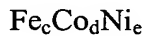


electrodes allowing a sense current to flow in a direction substantially perpendicular to the plane of the stack including the magnetization pinned layer, the nonmagnetic intermediate layer and the magnetization free layer,

wherein both of the magnetization pinned layer and the magnetization free layer has a laminate structure comprising alternately laminated layers of:

- (i) an alloy represented by general formula given below:



where $0 < c \leq 75$ at%, $0 < d \leq 75$ at%, $0 < e \leq 65$ at%, and $c + d + e = 100$; and

- (ii) at least one layer formed of at least one element selected from the group consisting of Cr, V, Ta, Nb, Sc, Ti, Mn, Cu, Zn, Ga, Ge, Zr, Hf, Y, Tc, Re, Ru, Rh, Ir, Pd, Pt, Ag, Au, B, Al, In, C, Si, Sn, Ca, Sr, Ba, O, N and F, and having a thickness falling within a range of between 0.03 nm and 1 nm.

26. (New) A magnetic head comprising the magnetoresistive device according to claim 25.

27. (New) A magnetic recording-reproducing apparatus, comprising a magnetic recording medium, and the magnetoresistive device according to claim 25.

REMARKS

Responsive to the Official Action dated April 16, 2003, Applicants provisionally elect, with traverse, Species 3-A, directed to a MR device wherein both of the pinned or free layers are laminate structures; where at least one of the free layer or the pinned layer comprising a Fe-rich alloy (i.e., the amount of Co and/or Ni in the claimed alloy is ≤ 50 at%),